

**IN THE CLAIMS:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A method of fabricating a display device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a gate insulating film on the semiconductor film;  
forming a gate wiring on the gate insulating film;  
forming a first ~~organic~~ leveling film containing a siloxane structure over the gate wiring;  
forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;  
forming a pixel electrode on the second ~~organic~~ leveling film; and  
forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL~~ layer over the pixel electrode,  
wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film.

2. (currently amended) A method of fabricating a display device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a gate insulating film on the semiconductor film;  
forming a gate wiring on the gate insulating film;  
forming a first ~~organic~~ leveling film containing a siloxane structure over the gate wiring;  
forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;  
forming a pixel electrode on the second ~~organic~~ leveling film; and

~~forming one of a layer selected from the group consisting of a liquid crystal layer and an EL layer over the pixel electrode,~~

wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film, and

wherein the thickness of the first ~~organic~~ leveling film is 0.1  $\mu\text{m}$  or more and less than 1.5  $\mu\text{m}$ .

3. (currently amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first ~~organic~~ leveling film containing a siloxane structure over the gate wiring;

forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;

forming a pixel electrode on the second ~~organic~~ leveling film; and

~~forming one of a layer selected from the group consisting of a liquid crystal layer and an EL layer over the pixel electrode,~~

wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film, and

wherein the thickness of the second ~~organic~~ leveling film is from 0.1  $\mu\text{m}$  to 2.9  $\mu\text{m}$  inclusive.

4. (currently amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;  
forming a first ~~organic~~ leveling film containing a siloxane structure over the gate wiring;  
forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;  
forming a pixel electrode on the second ~~organic~~ leveling film; and  
forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL~~ layer over the pixel electrode,  
wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film, and  
wherein the total thickness of the first ~~organic~~ leveling film and the second ~~organic~~ leveling film is from 0.2  $\mu\text{m}$  to 3.0  $\mu\text{m}$  inclusive.

5. (currently amended) A method of fabricating a display device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a gate insulating film on the semiconductor film;  
forming a gate wiring on the gate insulating film;  
forming a first ~~organic~~ leveling film containing a siloxane structure over the gate wiring;  
forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;  
forming a pixel electrode on the second ~~organic~~ leveling film; and  
forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL~~ layer over the pixel electrode,  
wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film, and

wherein the first ~~organic~~ leveling film and the second ~~organic~~ leveling film are insulating films formed by spin coating.

6. (currently amended) A method of fabricating a display device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a gate insulating film on the semiconductor film;  
forming a gate wiring on the gate insulating film;  
forming a wiring over the gate wiring;  
forming a first ~~organic~~ leveling film containing a siloxane structure over the gate wiring;  
forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;  
forming a pixel electrode on the second ~~organic~~ leveling film; and  
forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL layer~~ over the pixel electrode,  
wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film, ~~and~~  
~~wherein each of the first organic leveling film and the second organic leveling film comprises at least one of a polyimide resin and an acrylic resin.~~

7. (currently amended) A method of fabricating a display device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a gate insulating film on the semiconductor film;  
forming a gate wiring on the gate insulating film;  
forming a first ~~organic~~ leveling film containing a siloxane structure over the gate wiring;

forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;

forming a pixel electrode on the second ~~organic~~ leveling film; and

forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL~~ layer over the pixel electrode,

wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film, and

wherein the first ~~organic~~ leveling film and the second ~~organic~~ leveling film comprise the same material.

8. (currently amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first ~~organic~~ leveling film ~~comprising of a resin~~ containing a siloxane structure over the gate wiring;

forming a second ~~organic~~ leveling film ~~comprising of a resin~~ containing a siloxane structure on the first ~~organic~~ leveling film;

forming a pixel electrode on the second ~~organic~~ leveling film; and

forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL~~ layer over the pixel electrode,

wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film.

9. (currently amended) A method of fabricating a display device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming a gate insulating film on the semiconductor film;
- forming a gate wiring on the gate insulating film;
- forming an insulating film comprising an inorganic material over the gate insulating film;
- forming a first ~~organic~~ leveling film containing a siloxane structure over the insulating film;
- forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;
- forming a pixel electrode on the second ~~organic~~ leveling film; and
- forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL layer~~ over the pixel electrode,

wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film.

10. (currently amended) A method of fabricating a display device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming a gate insulating film on the semiconductor film;
- forming a gate wiring on the gate insulating film;
- applying a first layer ~~comprising resin~~ containing a siloxane structure by spin coating;
- baking the first layer to form a first ~~organic~~ leveling film;
- applying a second layer ~~comprising resin~~ containing a siloxane structure by spin coating;
- baking the second layer to form a second ~~organic~~ leveling film;
- forming a pixel electrode on the second ~~organic~~ leveling film; and
- forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL layer~~

layer over the pixel electrode,

wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film.

11. *previously*  
(canceled)

12. (currently amended) A The method according to claim 1, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

13. *previously*  
(canceled)

14. (currently amended) A The method according to claim 2, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

15. *previously*  
(canceled)

16. (currently amended) A The method according to claim 3, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

17. *previously*  
(canceled)

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18. (currently amended) A The method according to claim 4, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

19. (canceled) ✓

20. (currently amended) A The method according to claim 5, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

21. (canceled) ✓

22. (currently amended) A The method according to claim 6, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

23. (canceled) ✓

24. (currently amended) A The method according to claim 7, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

25. (canceled) ✓



26. (currently amended) A The method according to claim 8, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

27. (canceled) ✓

28. (currently amended) A The method according to claim 9, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

29. (canceled) ✓

30. (currently amended) A The method according to claim 10, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

31. (currently amended) A method of fabricating a display device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a gate insulating film on the semiconductor film;  
forming a gate wiring on the gate insulating film;  
forming a first inorganic film on the gate wiring;  
forming a wiring on the first inorganic film;  
forming a second inorganic film on the wiring;  
forming a first ~~organic~~ leveling film containing a siloxane structure on the second inorganic

film;

forming a second ~~organic~~ leveling film containing a siloxane structure on the first ~~organic~~ leveling film;

forming a pixel electrode on the second ~~organic~~ leveling film; and

forming ~~one of a layer selected from the group consisting of a liquid crystal layer and an EL~~ layer over the pixel electrode,

wherein the thickness of the first ~~organic~~ leveling film is thinner than that of the second ~~organic~~ leveling film.

32. (currently amended) A The method according to claim 31, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.